TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT process)

2SA1203

Audio Frequency Amplifier Applications

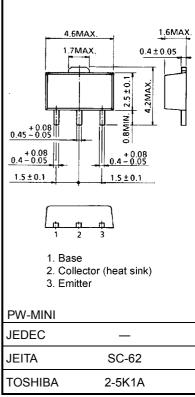
- Suitable for output stage of 3 watts amplifier
- Small flat package
- PC = 1.0 to 2.0 W (mounted on ceramic substrate)
- Complementary to 2SC2883

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit	
Collector-base voltage	V_{CBO}	-30	V	
Collector-emitter voltage	V_{CEO}	-30	V	
Emitter-base voltage	V_{EBO}	- 5	V	
Collector current	Ic	− 1.5	Α	
Base current	ΙΒ	-0.3	Α	
Collector power dissipation	PC	500	mW	
	P _C (Note 1)	1000		
Junction temperature	Tj	150	°C	
Storage temperature range	T _{stg}	-55 to 150	°C	

Note 1: Mounted on ceramic substrate (250 mm² × 0.8 t)

Unit: mm



Weight: 0.05 g (typ.)

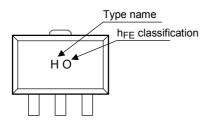


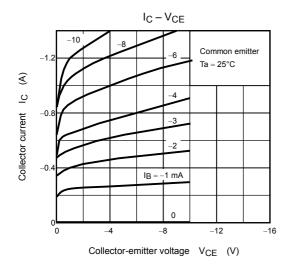
Electrical Characteristics (Ta = 25°C)

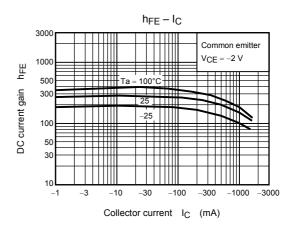
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	$V_{CB} = -30 \text{ V}, I_{E} = 0$	_	_	-0.1	μΑ
Emitter cut-off current	I _{EBO}	$V_{EB} = -5 \text{ V}, I_{C} = 0$	_	_	-0.1	μΑ
Collector-emitter breakdown voltage	V (BR) CEO	$I_C = -10 \text{ mA}, I_B = 0$	-30	_	_	V
Emitter-base breakdown voltage	V (BR) EBO	$I_E = -1 \text{ mA}, I_C = 0$	-5	_	_	V
DC current gain	h _{FE} (Note 2)	V _{CE} = -2 V, I _C = -500 mA	100	_	320	
Collector-emitter saturation voltage	V _{CE (sat)}	I _C = -1.5 A, I _B = -0.03 A	_	_	-2.0	V
Base-emitter voltage	V _{BE}	V _{CE} = -2 V, I _C = -500 mA	_	_	-1.0	V
Transition frequency	f _T	V _{CE} = -2 V, I _C = -500 mA	_	120	_	MHz
Collector output capacitance	C _{ob}	V _{CB} = −10 V, I _E = 0, f = 1 MHz	_	_	50	pF

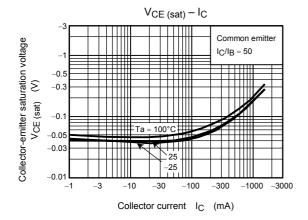
Note 2: $h_{\mbox{\scriptsize FE}}$ classification O: 100 to 200, Y: 160 to 320

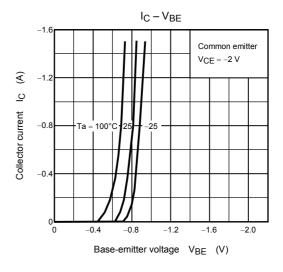
Marking

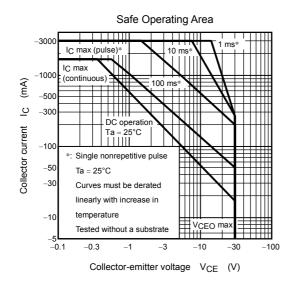


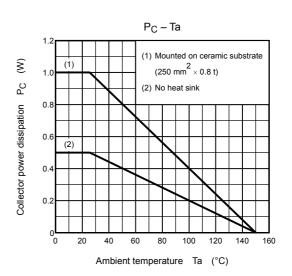












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